

**SEMICONDUCTOR
TECHNICAL DATA**

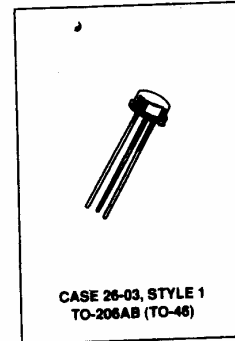
**2N3485A,
2N3486A**

**PNP Silicon
Small-Signal Transistors**

... designed for high-speed switching circuits and DC to VHF amplifier applications.

CRYSTALONCS
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Ronkonkoma, N.Y. 11779

MAXIMUM RATINGS			
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	60	V _{dc}
Collector-Base Voltage	V _{CBO}	60	V _{dc}
Emitter-Base Voltage	V _{EBO}	5.0	V _{dc}
Collector Current	I _C	600	mAdc
Power Dissipation	P _T	0.4	Watts
@ T _A = 25°C		2.28	mW/°C
Derate above 25°C		2.0	Watts
@ T _C = 25°C		11.43	mW/°C
Derate above 25°C			
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-65 to 200	°C



ELECTRICAL CHARACTERISTICS (T _A = 25°C unless otherwise noted.)				
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ⁽¹⁾ (I _C = 10 mAdc, I _B = 0)	V _{(BR)CEO}	60	—	V _{dc}
Collector-Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	V _{(BR)CBO}	60	—	V _{dc}
Base-Emitter Voltage (I _E = 10 μAdc, I _C = 0)	V _{(BR)EBO}	5.0	—	V _{dc}
Collector Cutoff Current (V _{CB} = 50 Vdc, I _E = 0)	I _{CBO}	—	10	nAdc
(V _{CB} = 50 Vdc, I _E = 0, T _A = 150°C)		—	10	μAdc
Emitter Cutoff Current (V _{EB} = 3.5 Vdc, I _C = 0)	I _{EBO}	—	50	nAdc

(1) Pulsed. Pulse Width 250 to 350 μs. Duty Cycle 1.0 to 2.0%.

(continued)

2N3485AJAN, 2N3486AJAN SERIES

ELECTRICAL CHARACTERISTICS — continued (T _A = 25 °C unless otherwise noted)					
Characteristic	Symbol	Min	Max	Unit	
ON CHARACTERISTICS					
DC Current Gain (I _C = 0.1 mA, V _{CE} = 10 Vdc)	2N3485A	40	—	—	
	2N3486A	75	—	—	
(I _C = 1.0 mA, V _{CE} = 10 Vdc)	2N3485A	40	—	—	
	2N3486A	100	—	—	
(I _C = 10 mA, V _{CE} = 10 Vdc)	2N3485A	40	—	—	
	2N3486A	100	—	—	
(I _C = 150 mA, V _{CE} = 10 Vdc) ⁽¹⁾	2N3485A	40	120	—	
	2N3486A	100	300	—	
(I _C = 500 mA, V _{CE} = 10 Vdc) ⁽¹⁾	2N3485A	40	—	—	
	2N3486A	50	—	—	
(I _C = 1.0 mA, V _{CE} = 10 Vdc, T _A = -65 °C)	2N3485A	20	—	—	
	2N3486A	40	—	—	
Collector-Emitter Saturation Voltage ⁽¹⁾ (I _C = 150 mA, I _B = 15 mA) (I _C = 500 mA, I _B = 50 mA)		V _{CE(sat)}	—	0.4 1.6	Vdc
Base-Emitter Saturation Voltage ⁽¹⁾ (I _C = 150 mA, I _B = 15 mA) (I _C = 500 mA, I _B = 50 mA)		V _{BE(sat)}	—	1.3 2.6	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current Gain (I _C = 1.0 mA, V _{CE} = 10 Vdc, f = 1.0 kHz)	2N3485A 2N3486A	h _{fe}	40 100	—	—
Small-Signal Current Transfer Ratio, Magnitude (I _C = 50 mA, V _{CE} = 20 Vdc, f = 100 MHz)		h _{fe}	2.0	10	—
Output Capacitance (V _{CB} = 10 Vdc, f = 0.1 to 1.0 MHz)		C _{obo}	—	8.0	pF
Input Capacitance (V _{EB} = 2.0 Vdc, f = 0.1 to 1.0 MHz)		C _{ibo}	—	30	pF
SWITCHING CHARACTERISTICS (See Figures 31 & 39)					
Turn-On Time	2N3485A 2N3486A	t _{on}	—	175	ns
Turn-Off Time		t _{off}	—	200	ns
Turn-On + Turn-Off Time (Non-Saturated Switching)		t _{on} + t _{off}	—	18	ns

ASSURANCE TESTING (Pre/Post Burn-In)				
Burn-In Conditions: T _A = +25 °C, V _{CB} = 30 Vdc				
P _T = 400 mW				
Characteristics Tested	Symbol	Initial and End Point Limits		Unit
		Min	Max	
Collector Cutoff Current (V _{CB} = 50 Vdc)	I _{CBO}	—	10	nAdc
DC Current Gain ⁽¹⁾ (I _C = 150 mA, V _{CE} = 10 Vdc)	2N3485A	40	120	—
	2N3486A	100	300	—
Delta from Pre-Burn-In Measured Values				
Delta Collector Cutoff Current	ΔI _{CBO}	—	±100 or ±5.0 whichever is greater	% of Initial Value nAdc
Delta DC Current Gain ⁽¹⁾	Δh _{FE}	—	±15	% of Initial Value

⁽¹⁾ Pulsed Pulse Width 250 to 350 μs Duty Cycle 1.0 to 2.0%